Silicon PNP Power Transistors 2SB1145

DESCRIPTION

- With TO-220F package
- High DC current gain.
- DARLINGTON
- Low collector saturation voltage

APPLICATIONS

- For high current driver and power driver applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

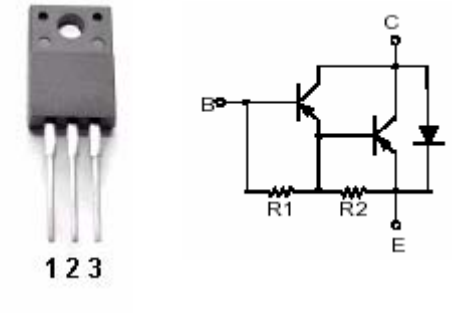

Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-5	A
P_C	Collector dissipation	T_C=25℃	20	W
		T_a=25℃	2	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-100 μ A; I_E=0	-120			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-5mA; I_B=0	-120			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.5A ; I_B=-3mA			-1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1.5A ; I_B=-3mA			-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V;I_E=0			-50	μ A
I_{EBO}	Emitter cut-off current	V_{EB}=-5V;I_C=0			-3.0	mA
h_{FE}	DC current gain	I_C=-1.5A ; V_{CE}=-3V	2000			

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PACKAGE OUTLINE

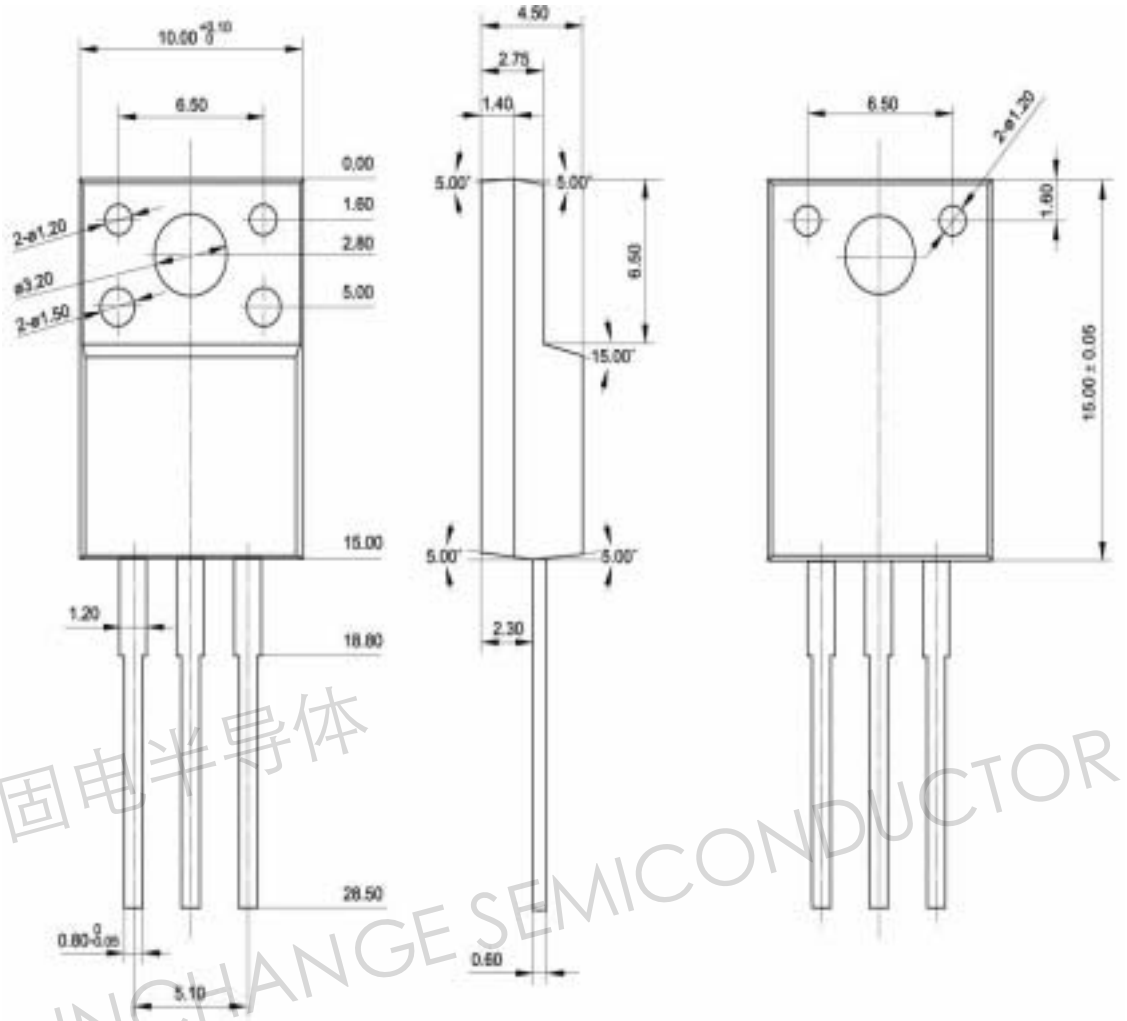

Fig.2 Outline dimensions